



# ACE6604B

## N-Channel Enhancement Mode Power MOSFET

### Description

ACE6604B uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### Features

- $V_{DS} = 60V$  ,  $I_D = 85A$
- $R_{DS(ON)}$  @  $V_{GS} = 10V$  , TYP=  $4.6m\Omega$
- $R_{DS(ON)}$  @  $V_{GS} = 4.5V$  , TYP=  $5.3m\Omega$

### Absolute Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise noted

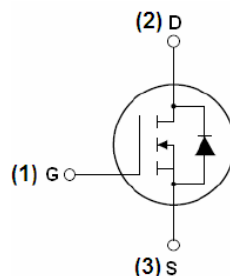
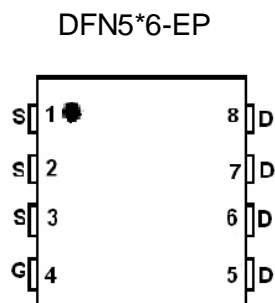
Parameter	Symbol	Max	Unit
Drain-Source Voltage	$V_{DSS}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current (Continuous)*AC	$I_D$	$T_A = 25^\circ C$	85
		$T_A = 100^\circ C$	54
Drain Current (Pulsed)*B	$I_{DM}$	340	A
Power Dissipation	$P_D$	135	W
Operating temperature / Storage temperature	$T_J / T_{STG}$	-55~150	$^\circ C$

A: The value of  $R_{\theta JA}$  is measured with the device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ C$ . The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the  $t \leq 10s$  junction to ambient thermal resistance rating.

### Packaging Type



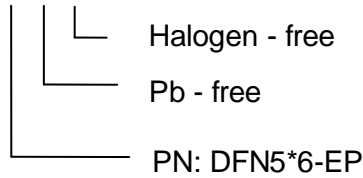


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### Ordering information

ACE6604B XX + H



### Electrical Characteristics T<sub>A</sub>=25°C, unless otherwise specified.

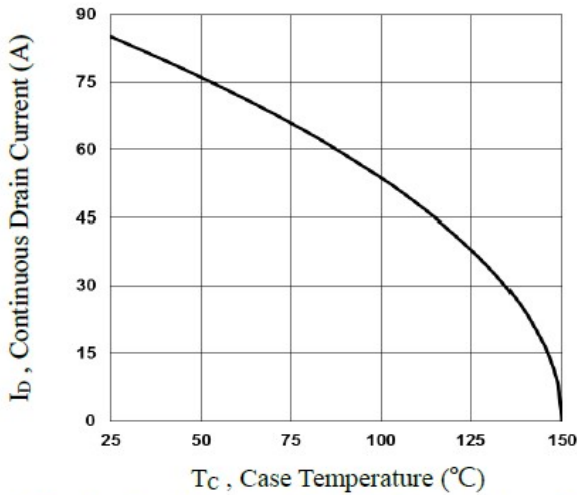
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$			1	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_{DS}=250\mu A$	1.2	1.6	2.5	V
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	$\mu A$
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=30A$		4.6	5.6	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$		5.3	7	
Forward Trans conductance	$g_{FS}$	$V_{DS}=10V, I_D=3A$		15		S
Diode forward voltage	$V_{SD}$	$I_{SD}=1A, V_{GS}=0V$			1.2	V
Maximum body-diode continuous current	$I_S$				85	A
<b>Switching</b>						
Total Gate Charge	$Q_g$	$V_{GS}=4.5V, V_{DS}=30V, I_D=10A$		33		nC
Gate-Source Charge	$Q_{gs}$			11		
Gate-Drain Charge	$Q_{gd}$			12		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A, V_{GS}=10V, R_G=3.3\Omega$		21		ns
Turn-on Rise Time	$t_r$			17		
Turn-off Delay Time	$t_{d(off)}$			72		
Turn-off Fall Time	$t_f$			21		
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$		4750		pF
Output Capacitance	$C_{oss}$			330		
Reverse Transfer Capacitance	$C_{rss}$			161		



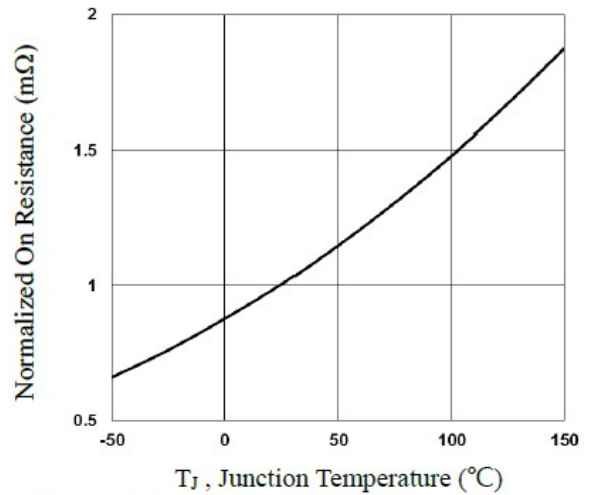
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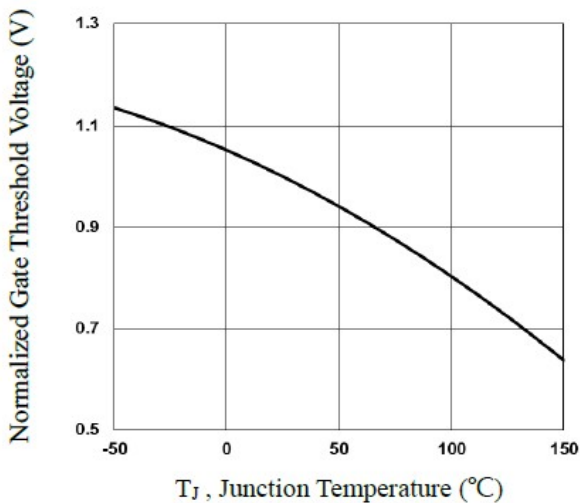
### Typical Performance Characteristics



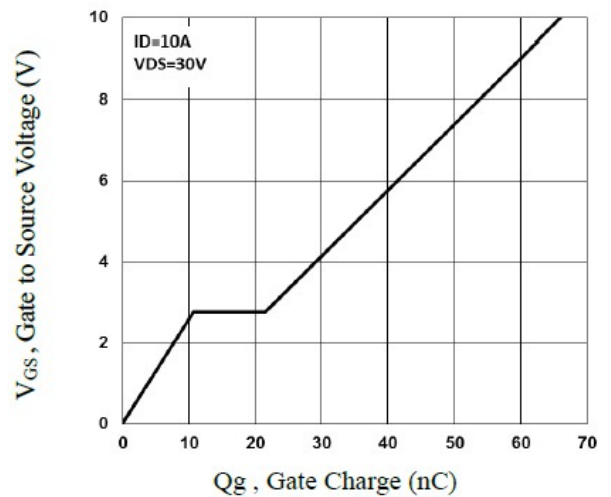
**Fig.1 Continuous Drain Current vs.  $T_C$**



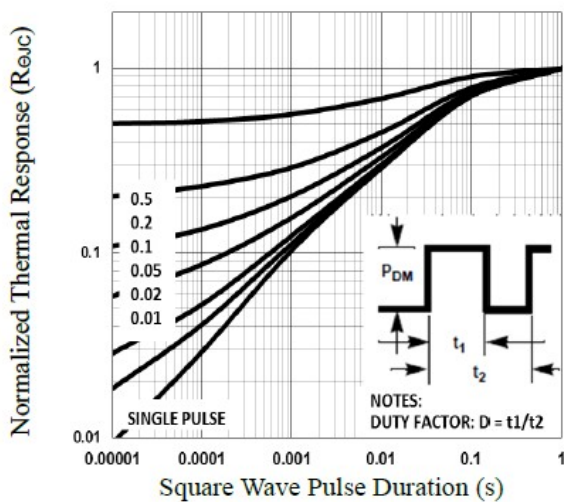
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$**



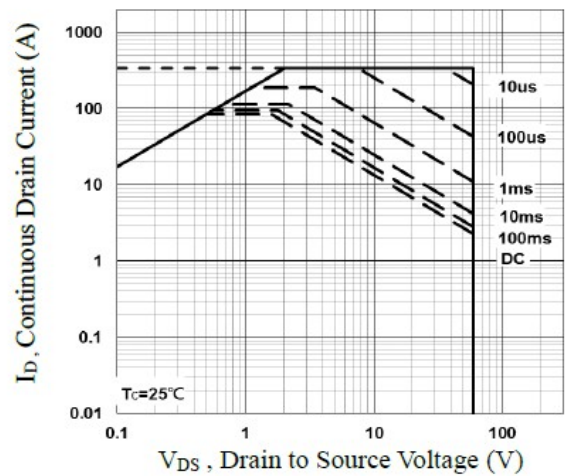
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



**Fig.4 Gate Charge Waveform**



**Fig.5 Normalized Transient Response**



**Fig.6 Maximum Safe Operation Area**

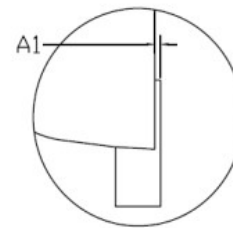
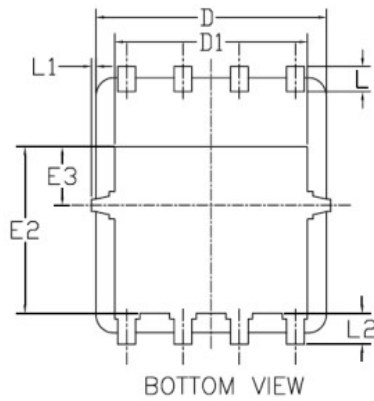
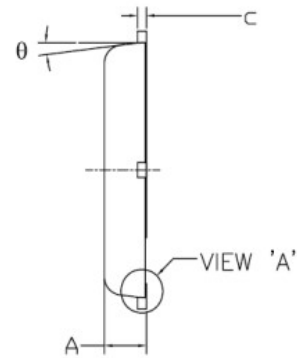
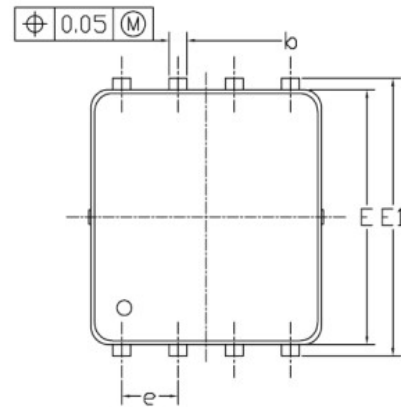


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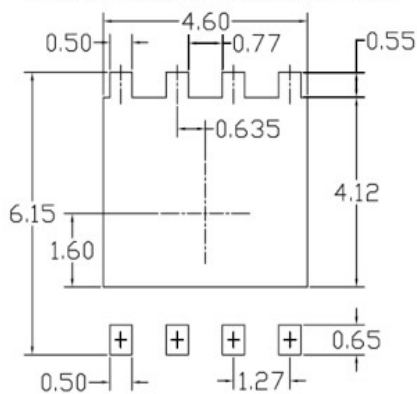
### Packing Information

#### DFN5\*6-EP



VIEW 'A'  
(SCALE 5:1)

#### RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	—	0.05	0.000	—	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.625 BSC			0.143 BSC		
E3	1.275 BSC			0.050 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	—	0.15	0	—	0.006
L2	0.68 REF			0.027 REF		
θ	0°	—	10°	0°	—	10°

UNIT: mm

#### NOTE

- PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- CONTROLLING DIMENSION IS MILLIMETER.  
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



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### Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.